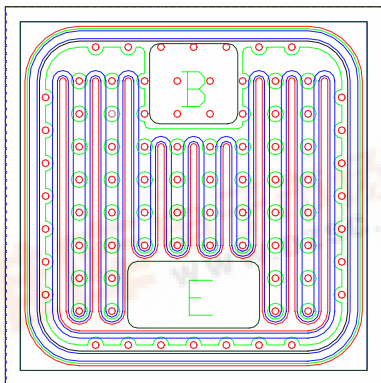


C2328 Silicon NPN Epitaxial Transistor

Description: The C2328 is designed for use in power amplifier applications and power switching applications

- Features:
- Low collector saturation voltage
 - Complementary to A1020

Chip Appearance

	Chip Size		760um×760um
	Chip Thickness		210±20um
	Bonding Pad Size	Base	160×170um
		Emitter	130×260um
	Front Metal		Al
	Backside Metal		Au(As)
	Scribe line width		60um
	Wafer Size		6 inch

Electrical Characteristics(Ta=25°C)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB}=30V, I_E=0$		0.1	uA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=5V, I_C=0$		0.1	uA
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C=0.1mA$	30		V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C=10mA$	30		V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E=0.1mA$	5.0		V
DC Current Gain	h_{FE}	$V_{CE}=2V, I_C=0.5A$	80	400	
Collector Saturation Voltage	$V_{CE(sat)}$	$I_C=1A, I_B=50mA$		0.5	V

